

21	15967	((356/399, 400, 401, 388, 614).CCLS.) ((250/492.2, 491.1, 548, 559.29, 559.3, 559.36).CCLS.) ((355/53, 55, 67, 77).CCLS.) ((430/22, 30, 5).CCLS.) ((382/151).CCLS.) ((438/401, 401, 388, 614).CCLS.) ((250/492.2, 491.1, 548, 559.29, 559.3, 559.36).CCLS.) ((355/53, 55, 67, 77).CCLS.) ((430/22, 30, 5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same ((photomask mask reticle) same (wafer semiconduct\$ substrate))) and (((mask photomask reticle) same phase) same ("0"))	USPAT; US-PPGPUB	2004/04/29 11:19
22	3717	((356/399, 400, 401, 388, 614).CCLS.) ((250/492.2, 491.1, 548, 559.29, 559.3, 559.36).CCLS.) ((355/53, 55, 67, 77).CCLS.) ((430/22, 30, 5).CCLS.) ((382/151).CCLS.) ((438/401, 401, 388, 614).CCLS.) ((250/492.2, 491.1, 548, 559.29, 559.3, 559.36).CCLS.) ((355/53, 55, 67, 77).CCLS.) ((430/22, 30, 5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same ((photomask mask reticle) same (wafer semiconduct\$ substrate))) and (((mask photomask reticle) same phase) same ("0"))	USPAT; US-PPGPUB	2004/04/29 11:19
23	1026	\$em18564000\$400p401\$1a800\$)514).CCLS.) ((250/492.2, 491.1, 548, 559.29, 559.3, 559.36).CCLS.) ((355/53, 55, 67, 77).CCLS.) ((430/22, 30, 5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same ((photomask mask reticle) same (wafer semiconduct\$ substrate))) and (((mask photomask reticle) same phase) same ("0"))	USPAT; US-PPGPUB	2004/04/29 11:20
24	308	\$phot0m4s8999\$101\$3m8, \$phot4\$e\$CCLS.) ((250/492.2, 491.1, 548, 559.29, 559.3, 559.36).CCLS.) ((355/53, 55, 67, 77).CCLS.) ((430/22, 30, 5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same ((photomask mask reticle) same (wafer semiconduct\$ substrate))) and (((mask photomask reticle) same phase) same ("0"))	USPAT; US-PPGPUB	2004/04/29 11:27
25	80	'18035p1\$99, 400, 401, 388, 614).CCLS.) ((250/492.2, 491.1, 548, 559.29, 559.3, 559.36).CCLS.) ((355/53, 55, 67, 77).CCLS.) ((430/22, 30, 5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same ((photomask mask reticle) same (wafer semiconduct\$ substrate))) and (((mask photomask reticle) same phase) same ("0"))	USPAT; US-PPGPUB	2004/04/29 11:33
26	45	'180'3p6)399am00a100gn\$8, 614).CCLS.) ((250/492.2, 491.1, 548, 559.29, 559.3, 559.36).CCLS.) ((355/53, 55, 67, 77).CCLS.) ((430/22, 30, 5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same ((photomask mask reticle) same (wafer semiconduct\$ substrate))) and (((mask photomask reticle) same phase) same ("0")) "180" pi) same align\$)) and ((align\$ near (mark\$ pattern\$ target\$ grat\$3)) \$4m001WaHBNsemicond\$ substrate))	USPAT; US-PPGPUB	2004/04/29 12:26
27	16		USPAT	2004/04/29 11:58
29	34	carpi.in.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/29 12:30
30	1	2003-755598.NRAN.	DERWENT	2004/04/29 12:28
31	87	liegl.in.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/29 12:32
32	2	(bernhard and liegl).in.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/29 12:30
33	17	thwaite.in.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/29 12:32